

## PRODUCT / PROCESS CHANGE NOTIFICATION

### 1. PCN basic data

1.1 Company	 STMicroelectronics International N.V
1.2 PCN No.	ADG/23/14279
1.3 Title of PCN	L9788 (UR66) - Additional Diffusion Site Activation (Singapore)
1.4 Product Category	L9788, L9788TR
1.5 Issue date	2023-10-01

### 2. PCN Team

2.1 Contact supplier	
2.1.1 Name	ROBERTSON HEATHER
2.1.2 Phone	+1 8475853058
2.1.3 Email	heather.robertson@st.com
2.2 Change responsibility	
2.2.1 Product Manager	Vito GRAZIANO
2.2.2 Marketing Manager	Francesco MACINA, Tony BARBUZZI
2.2.3 Quality Manager	Marcello Donato MENCHISE

### 3. Change

3.1 Category	3.2 Type of change	3.3 Manufacturing Location
Transfer	Line transfer for a full process or process brick (process step, control plan, recipes) from one site to another site: Wafer fabrication	ST Ang Mo Kio - Singapore receiving Site

### 4. Description of change

	Old	New
4.1 Description	ST Agrate - Italy Diffusion Site	ST Agrate - Italy and Ang Mo Kio - Singapore Diffusion Sites
4.2 Anticipated Impact on form, fit, function, quality, reliability or processability?	No Impact	

### 5. Reason / motivation for change

5.1 Motivation	Service and Capacity improvement
5.2 Customer Benefit	CAPACITY INCREASE

### 6. Marking of parts / traceability of change

6.1 Description	Dedicated Finished Good Code
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### 7. Timing / schedule

7.1 Date of qualification results	2024-12-29
7.2 Intended start of delivery	2025-01-31
7.3 Qualification sample available?	Upon Request

### 8. Qualification / Validation

8.1 Description		
8.2 Qualification report and qualification results	In progress	Issue Date

### 9. Attachments (additional documentations)

14279 Public product.pdf
14279 Details.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
	L9788TR	

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## PRODUCT/PROCESS CHANGE NOTIFICATION

<b>TITLE</b>	L9788 (UR66) - Additional Diffusion Site Activation (Singapore)																																			
<b>IMPACTED PRODUCTS</b>	<p>ST Line UR66 diffused in BCD9SL technology and assembled in LQFP-EP 100 14x14 package:</p> <ul style="list-style-type: none"> <li>✚ L9788</li> <li>✚ L9788TR</li> </ul>																																			
<b>MANUFACTURING STEP</b>	Silicon diffusion																																			
<b>INVOLVED PLANT</b>	ST Singapore (Ang Mo Kio) – Recipient Site																																			
<b>CHANGE REASON</b>	Service and Capacity improvement																																			
<b>CHANGE DESCRIPTION</b>	Activation of ST Singapore (Ang Mo Kio) silicon diffusion site beside current one ST Agrate – Italy.																																			
<b>TRACEABILITY</b>	Dedicated Finished Good Code																																			
<b>VALIDATION</b>	<p>Validation as per ZVEI guidelines, item SEM-PW-13: Move all or parts of production to a different wafer fab site, leading to following qualification plan:</p> <table border="1" data-bbox="481 1393 1403 1584"> <thead> <tr> <th>AEC Q100 &amp; ZVEI requirement</th> <th>Group A</th> <th>Group B</th> <th>Group C</th> <th>Group D</th> <th>Group E</th> <th>Group F</th> <th>Extra AEC-Q100</th> </tr> </thead> <tbody> <tr> <td>Test Name</td> <td>PC THB<sup>1</sup> AC<sup>1</sup> TC<sup>1</sup> PTC<sup>1</sup> HTSL</td> <td>HTOL<sup>1</sup> ELFR EDR</td> <td>WBP WBS SD FD SBS LI</td> <td>EM TDBB HCI HBN<sup>1</sup> SM</td> <td>HBM CDM LI ED</td> <td>CHAR EMC SC SER LF</td> <td>SBY PAT</td> <td>Whisker test Parameter Analysis</td> </tr> <tr> <td>Wafer fab site SEM-PW-13</td> <td>• • • • •</td> <td>• • -</td> <td>• • - - -</td> <td>• • • • •</td> <td>• • • - -</td> <td>- - - - -</td> <td>• •</td> <td>• •</td> </tr> <tr> <td>Cu wire Q006</td> <td>• • - • •</td> <td>- - -</td> <td>• • - - -</td> <td>- - -</td> <td>- - -</td> </tr> </tbody> </table> <p>1. Tests preceded by PC &gt; 100 cycles @ -55/+150°C 2. Tests in AEC-Q100 Group G are not applicable</p> <p>see below details.</p>	AEC Q100 & ZVEI requirement	Group A	Group B	Group C	Group D	Group E	Group F	Extra AEC-Q100	Test Name	PC THB <sup>1</sup> AC <sup>1</sup> TC <sup>1</sup> PTC <sup>1</sup> HTSL	HTOL <sup>1</sup> ELFR EDR	WBP WBS SD FD SBS LI	EM TDBB HCI HBN <sup>1</sup> SM	HBM CDM LI ED	CHAR EMC SC SER LF	SBY PAT	Whisker test Parameter Analysis	Wafer fab site SEM-PW-13	• • • • •	• • -	• • - - -	• • • • •	• • • - -	- - - - -	• •	• •	Cu wire Q006	• • - • •	- - -	• • - - -	- - - - -	- - - - -	- - - - -	- - -	- - -
AEC Q100 & ZVEI requirement	Group A	Group B	Group C	Group D	Group E	Group F	Extra AEC-Q100																													
Test Name	PC THB <sup>1</sup> AC <sup>1</sup> TC <sup>1</sup> PTC <sup>1</sup> HTSL	HTOL <sup>1</sup> ELFR EDR	WBP WBS SD FD SBS LI	EM TDBB HCI HBN <sup>1</sup> SM	HBM CDM LI ED	CHAR EMC SC SER LF	SBY PAT	Whisker test Parameter Analysis																												
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<b>CURRENT PRODUCTS</b>	Following activation of product diffusion in Singapore, device will be available from both diffusion sites, depending on ST production requirements.																																			
<b>REPORTS</b>	Qualification activity is in progress; validation reports are expected to be available by Q4-2024																																			

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## Q100 Qualification Test Plan

QP001423CS2039\_01

Automotive Grade Level = 1 -40 to +125C MSL = 3

<b>Supplier Name:</b>	STMicroelectronics	<b>General Specification:</b>	AEC-Q100 Rev. H
<b>Supplier Code:</b>	UR66	<b>Supplier Wafer Fabrication:</b>	Singapore (SG8E)
<b>Supplier Part Number:</b>	L9788	<b>Supplier Wafer Test:</b>	Singapore (SG8E)
<b>Supplier Contact:</b>	D. Bini / R. Alberti	<b>Supplier Assembly Site:</b>	Muar
<b>Supplier Family Type:</b>	BCD9sL / LQFP100 exp pad down (Cu wires 1.2/2mils)	<b>Supplier Final Test Site:</b>	Muar
<b>Device Description:</b>	IC for engine management system	<b>Supplier Reliability Signature:</b>	D. Bini
<b>PPAP Submission Date:</b>		<b>Customer Test ID:</b>	
<b>Reason for Qualification:</b>	Diffusion plant transfer	<b>Customer Part Number:</b>	
<b>Prepared by Signature:</b>	R. Alberti	<b>Customer Approval Signature:</b>	

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## Q100 and ZVEI requirements

AEC Q100 & ZVEI requirement	Group A		Group B		Group C				Group D				Group E						Group F		Extra AEC-Q100																
Test Name	PC	THB <sup>1</sup>	AC <sub>1</sub>	TC <sub>1</sub>	PTC <sup>1</sup>	HTSL	HTOL <sup>1</sup>	ELFR	EDR	WBP	WBS	SD	PD	SBS	LI	EM	TDDB	HCI	NBTI	SM	HBM	CDM	LU	ED	FG	CHAR	EMC	SC	SER	LF	SBY	PAT	Whisker test	Parameter-Analysis			
Wafer fab site SEM-PW-13	•	•	•	•	•	•	-	•	•	-	•	-	-	-	-	•	•	•	•	•	•	•	•	-	-	-	-	-	•	•	-	-	•	•	-	-	
Cu wire Q006	•	•	-	•	•	•	-	-	-	•	•	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-

1. Tests preceded by PC + 100 cycles @ -55/+150C

2. Tests in AEC-Q100 Group G are not applicable

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Test	#	Reference	Test Conditions	Requirements			Comments	UR66	Notes
				Lots	S.S.	Total			
PC	A1	JESD22 A113 J-STD-020	Preconditioning: (Test @ Rm) SMD only Moisture Preconditioning for THB, AC, TC, PTC, HTOL, HTRB Peak Reflow Temp = 260°C	All surface mount parts prior to A2, A3, A4, A5, B1		MSL = 3	Planned		+100 cycles after reflow.
THB	A2	JESD22 A110	Temperature Humidity Bias: (Test @ Rm/Hot) 85°C, 85% Target: 1000h Q006: 2000h	3	77	231	-	1 lot TTTT-LL 1 lot LLTT-HH+10% 1 lot TTLT-LL	Extension up to 2000h for Q006.
AC	A3	JESD22 A118	Autoclave: (Test @ Rm) 121°C / 2 atm Target: 96h	3	77	231	-	1 lot TTTT-LL 1 lot LLTT-LL 1 lot TTLT-LL	
TC	A4	JESD22 A104	Temperature Cycle: (Test @ Hot) -55/+150°C Target: 1000cy Q006: 2000cy	6	77	462	-	1 lot TTTT-LL 1 lot TTTT-HH+10% 1 lot LLTT-LL 1 lot LLTT-HH+10% 1 lot TTLT-LL 1 lot TTLT-HH+10%	Extension up to 2000cy for Q006.
PTC	A5	JESD22 A105	Power Temperature Cycle: (Test @ Room/Hot) Ta=-40°C / Tj = +150°C Target: 1000cy Q006: 2000cy	2	23	45	-	1 lot TTTT-LL 1 lot TTTT-HH+10%	Extension up to 2000cy for Q006.
HTSL	A6	JESD22 A103	High Temperature Storage Life: (Test @ Rm/Hot) 175°C Target: 500h Q006: 1000h	3	45	135	-	1 lot TTTT-LL 1 lot LLTT-LL 1 lot TTLT-LL	Extension up to 1000h for Q006.

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Test	#	Reference	Test Conditions	Requirements			Comments	UR66	Notes
				Lots	S.S.	Total			
HTOL	B1	JESD22 A108	High Temp Operating Life: (Test @ Rm/Cold/Hot) T <sub>j</sub> 175°C  Target: 1556h	3	77	231	-	1 lot TTTT-HH+10% 1 lot LLTT- HH+10% 1 lot TTLT-HH+10%	
ELFR	B2	AEC-Q100-008	Early Life Failure Rate: (Test @ Rm/Hot)	3	800	2400	-	-	Replaced by Safe launch data.
EDR	B3	AEC-Q100-005	NVM Endurance & Data Retention Test: (Test @ Rm/Hot)	-	-	-	-	-	N/A.
WBS	C1	AEC-Q100-001 AEC-Q003	Wire Bond Shear Test: (Cpk > 1.67)	30 bonds 5 parts Min.			-	Assembly data and according to Q100 and Q006	
WBP	C2	Mil-STD-883, Method 2011 AEC-Q003	Wire Bond Pull: (Cpk > 1.67); Each bonder used	30 bonds 5 parts Min.			-	Assembly data and according to Q100 and Q006	
SD	C3	JESD22 B102 JSTD-002D	Solderability: (>95% coverage) 8hr steam aging prior to testing	1	15	15	-	Assembly data	
PD	C4	JESD22 B100, JESD22 B108 AEC-Q003	Physical Dimensions: (Cpk > 1.67)	3	10	30	-	Assembly data	
SBS	C5	AEC-Q100-010 AEC-Q003	Solder Ball Shear: (Cpk > 1.67); 5 balls from min. of 10 devices	3	50 balls	-	-	-	N/A.
LI	C6	JESD22 B105	Lead Integrity: (No lead cracking or breaking); Through-hole only; 10 leads from each of 5 devices	1	50 leads	-	-	-	N/A.
EM	D1	JESD61	Electromigration	-	-	-	-	-	Process qualification data.
TDDB	D2	JESD35	Time Dependant Dielectric Breakdown	-	-	-	-	-	Process qualification data.
HCI	D3	JESD60 & 28	Hot Carrier Injection	-	-	-	-	-	Process qualification data.

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Test	#	Reference	Test Conditions	Requirements			Comments	UR66	Notes
				Lots	S.S.	Total			
NBTI	D4	JESD90	Negative Bias Temperature Instability	-	-	-	-	-	Process qualification data.
SM	D5	JESD61, 87, & 202	Stress Migration	-	-	-	-	-	Process qualification data.
TEST	E1	User/Supplier Specification	Pre and Post Stress Electrical Test:	All	All	All	-	-	
HBM	E2	AEC-Q100-002	Electrostatic Discharge, Human Body Model: (Test @ Rm/Hot); (2kV HBM / Class 2 or better)	-	-	-	-	1 lot	For Global pins 4kV vs GND.
CDM	E3	AEC-Q100-011	Electrostatic Discharge, Charged Device Model: (Test @ Rm/Hot); (750V corner leads, 500V all other leads / Class C4B or better)	-	-	-	-	1 lot	
LU	E4	AEC-Q100-004	Latch-Up: (Test @ Rm/Hot)	-	-	-	-	1 lot	
ED	E5	AEC-Q100-009 AEC-Q003	Electrical Distributions: (Test @ Rm/Hot/Cold) (where applicable, Cpk >1.67)	3	30	90	-	Planned	Covered by Electrical Characterization.
FG	E6	AEC-Q100-007	Fault Grading FG shall be = or > 90% for qual units	-	-	-	-	-	
CHAR	E7	AEC-Q003	Characterization: (Test @ Rm/Hot/Cold)	-	-	-	-	-	Covered by Electrical Characterization.
EMC	E9	SAE J1752/3	Electromagnetic Compatibility (Radiated Emissions)	-	-	-	-	-	
SC	E10	AEC Q100-012	Short Circuit Characterization	-	-	-	-	-	N/A.
SER	E11	JESD89-1 JESD89-2 JESD89-3	Soft Error Rate	-	-	-	-	-	N/A.

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Test	#	Reference	Test Conditions	Requirements			Comments	UR66	Notes
				Lots	S.S.	Total			
LF	E12	AEC-Q005	Lead (Pb) Free: (see AEC-Q005)	-	-	-	-	-	Covered by Test group A & C.
PAT	F1	AEC-Q001	Process Average Testing: (see AEC-Q001)	All	All	All	Reject units outside Avg.	-	Applied in production.
SBA	F2	AEC-Q002	Statistical Bin/Yield Analysis: (see AEC-Q002)	All	All	All	Reject units outside criteria	-	Applied in production.
MS	G1	JESD22 B104	Mechanical Shock: (Test @ Rm)	1	15	15	-	-	N/A.
VFV	G2	JESD22 B103	Variable Frequency Vibr: (Test @ Rm)	1	15	15	-	-	N/A.
CA	G3	MIL-STD-883 Method 2001	Constant Acceleration: (Test @ Rm)	1	15	15	-	-	N/A.
GFL	G4	MIL-STD-883 Method 1014	Gross and Fine Leak:	1	15	15	-	-	N/A.
DROP	G5	-----	Drop Test: (Test @ Rm) MEMS cavity parts only. Drop part on each of 6 axes once from a height of 1.2m onto a concrete surface.	1	5	5	-	-	N/A.
LT	G6	MIL-STD-883 Method 2004	Lid Torque	1	5	5	-	-	N/A.
DS	G7	MIL-STD-883 Method 2019	Die Shear	1	5	5	-	-	N/A.
IWV	G8	MIL-STD-883 Method 1018	Internal Water Vapor	1	5	5	-	-	N/A.
HTRB	-	JESD22 A108	High Temperature Reverse Bias: (Test @ Rm) T <sub>j</sub> =150°C Target: 1000h	1	45	45	-	1 lot TTTT-HH+10%	

## Public Products List

Public Products are off the shelf products. They are not dedicated to specific customers, they are available through ST Sales team, or Distributors, and visible on ST.com

**PCN Title :** L9788 (UR66) - Additional Diffusion Site Activation (Singapore)

**PCN Reference :** ADG/23/14279

**Subject :** Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

L9788TR	L9788	
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